2SB0792

Silicon PNP epitaxial planar type

For high breakdown voltage low-noise amplification

Features

- High collector-emitter voltage (Base open) V_{CEO}
- · Low noise voltage NV
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing.

Absolute Maximum Ratings $T_a = 25^{\circ}C$

				2.0011			
Parameter	Symbol	Rating	Unit				
Collector-base voltage (Emitter open)	V _{CBO}	-150	V	Markir	ng Symb		
Collector-emitter voltage (Base open)	V _{CEO}	-150	V			1	
Emitter-base voltage (Collector open)	V _{EBO}	-5	V				
Collector current	I _C	-50	mA			<u></u>	
Peak collector current	I _{CP}	-100	mA			. All	
Collector power dissipation	P _C	200	mW		Ì,		
Junction temperature	Tj	150	°C		S		
Storage temperature	T _{stg}	-55 to +150	°C		6,05		
• •				, il	SCIE		
Collector-emitter voltage (Base open) V_{CEO} -150 V Emitter-base voltage (Collector open) V_{EBO} -5 V Collector current I_C -50 mA Peak collector current I_{CP} -100 mA Collector power dissipation P_C 200 mW Junction temperature T_j 150 $°C$ Storage temperature T_{ste} -55 to $+150$ $°C$ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$ 200 n_{CO}							
Parameter	Symb	ol	Conditions	anil	Min	Тур	Max
Collector-emitter voltage (Base open)	VCEO	$I_{\rm C} = -100$	μΑ, Ι _B =0	3	-150		
					1	1	

Electrical Characteristics T_a = 25°C±3°C

Parameter	Symbol		Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -100 \mu$	$IA, I_B = 0$	-150			V
Emitter-base voltage (Collector open)	V _{EBO}	$I_{\rm E} = -10 \mu$	$A_{\rm v} V_{\rm C} = 0$	-5			V
Collector-base cutoff current (Emitter open)	I _{CBO}	V _{CB} = -10	$0 \text{ V}, \text{I}_{\text{E}} \neq 0$			-1	μΑ
Forward current transfer ratio *	h _{FE}	$V_{CE} = -5 V$	√1 −10 mA	130		450	
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -30 {\rm m}$	A, $I_B = -3 \text{ mA}$			-1	V
Transition frequency	f	$V_{CB} = -10$	V, $I_E = 10 \text{ mA}$, f = 200 MHz		200		MHz
Collector output capacitance (Common base, input open circuited)	Cob	$V_{CB} = -10$	$V, I_E = 0, f = 1 MHz$		4		pF
Noise voltage	NV	CD	V, $I_C = -1$ mA, $G_V = 80$ dB, Ω , Function = FLAT		150		mV

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	R	S	Т
$h_{\rm FE}$	130 to 220	185 to 330	260 to 450
Merking symbol	IR	IS	IT



Package

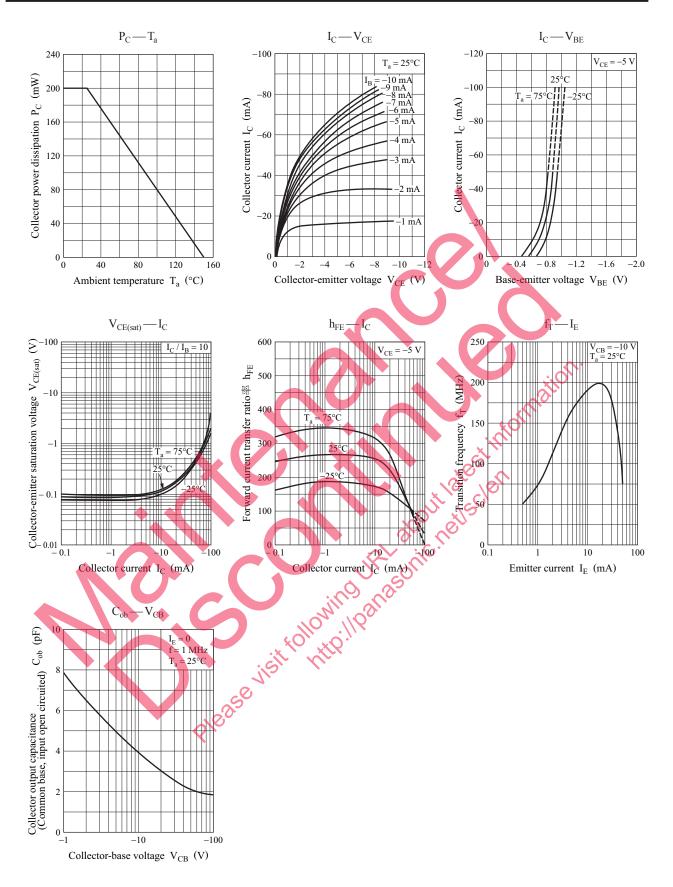
• Pin Name

1. Base

 Code Mini3-G1

2SB0792

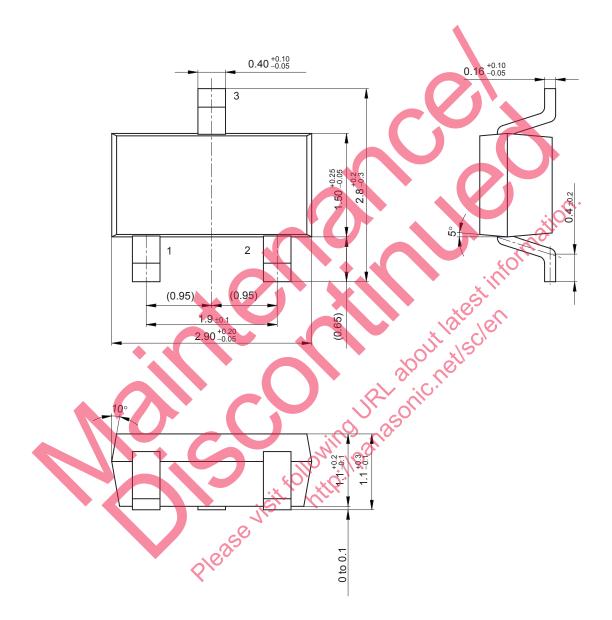
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Unit: mm



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